**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- · Trench MOSFET technology
- · Side wettable flanks for optical solder inspection
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- · AEC-Q101 qualified

## 3. Applications

- · Relay driver
- · High-speed line driver
- High-side load switch
- · Switching circuits

#### 4. Quick reference data

Table 1. Quick reference data

| Symbol            | Parameter                        | Conditions  |     | Min | Тур | Max  | Unit |
|-------------------|----------------------------------|---|-----|-----|-----|------|------|
| V <sub>DS</sub>   | drain-source voltage             | T <sub>j</sub> = 25 °C                            |     | -   | -   | -30  | V    |
| $V_{GS}$          | gate-source voltage              |   |     | -20 | -   | 20   | V    |
| I <sub>D</sub>    | drain current                    | V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C | [1] | -   | -   | -4.7 | Α    |
| Static characte   | Static characteristics           |   |     |     |     |      |      |
| R <sub>DSon</sub> | drain-source on-state resistance | $V_{GS}$ = -10 V; $I_D$ = -4.7 A; $T_j$ = 25 °C   |     | -   | 40  | 50   | mΩ   |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

#### **Table 2. Pinning information**

| Pin | Symbol | Description | Simplified outline    | Graphic symbol |
|-----|--------|-------------|-----------------------|----------------|
| 1   | D      | drain       | 1 6                   | D              |
| 2   | D      | drain       |                       |                |
| 3   | G      | gate        | 2 5                   | G P            |
| 4   | S      | source      | 3 8 94                | S              |
| 5   | D      | drain       | Transparent top view  | 017aaa257      |
| 6   | D      | drain       | DFN2020MD-6 (SOT1220) |                |
| 7   | D      | drain       |                       |                |
| 8   | S      | source      |                       |                |

# 6. Ordering information

**Table 3. Ordering information** 

| Type number | Package     |   |         |  |  |  |
|-------------|-------------|---|---------|--|--|--|
|             | Name        | Description   | Version |  |  |  |
| PMPB48EPA   | DFN2020MD-6 | DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals | SOT1220 |  |  |  |

# 7. Marking

### **Table 4. Marking codes**

| Type number | Marking code |
|-------------|--------------|
| PMPB48EPA   | 4Q           |

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# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol               | Parameter   | Conditions  |     | Min | Max  | Unit |
|----------------------|---|---|-----|-----|------|------|
| $V_{DS}$             | drain-source voltage                                | T <sub>j</sub> = 25 °C  |     | -   | -30  | V    |
| $V_{GS}$             | gate-source voltage                                 |   |     | -20 | 20   | V    |
| I <sub>D</sub>       | drain current                                       | V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C                   | [1] | -   | -4.7 | Α    |
|                      |   | V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 100 °C                  | [1] | -   | -3   | Α    |
| I <sub>DM</sub>      | peak drain current                                  | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$                 |     | -   | -19  | Α    |
| P <sub>tot</sub>     | total power dissipation                             | T <sub>amb</sub> = 25 °C  | [1] | -   | 1.7  | W    |
|                      |   | T <sub>sp</sub> = 25 °C   |     | -   | 12.5 | W    |
| Tj                   | junction temperature                                |   |     | -55 | 150  | °C   |
| T <sub>amb</sub>     | ambient temperature                                 |   |     | -55 | 150  | °C   |
| T <sub>stg</sub>     | storage temperature                                 |   |     | -65 | 150  | °C   |
| Source-drain di      | ode   |   |     |     |      |      |
| I <sub>S</sub>       | source current                                      | T <sub>amb</sub> = 25 °C  | [1] | -   | -1.8 | Α    |
| ESD maximum          | rating  |   |     |     |      |      |
| $V_{ESD}$            | electrostatic discharge voltage                     | НВМ   | [2] | -   | 500  | V    |
| Avalanche rugg       | jedness   |   | ·   |     |      |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-<br>source avalanche<br>energy | $T_{j(init)}$ = 25 °C; $I_D$ = -1.1 A; DUT in avalanche (unclamped) |     | -   | 17.3 | mJ   |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

<sup>[2]</sup> Measured between all pins.

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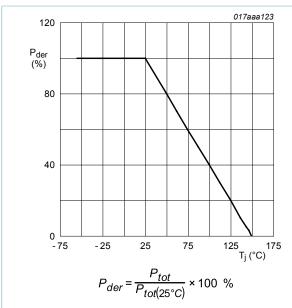


Fig. 1. Normalized total power dissipation as a function of junction temperature

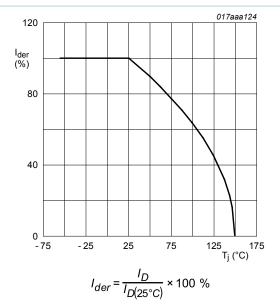
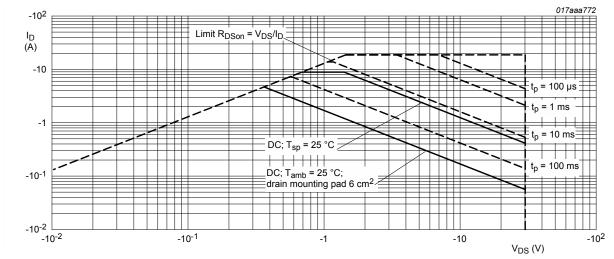


Fig. 2. Normalized continuous drain current as a function of junction temperature



I<sub>DM</sub> = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

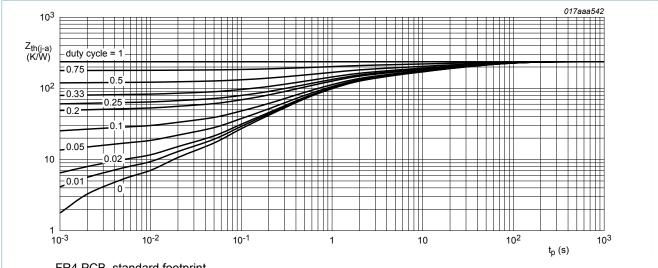
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### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

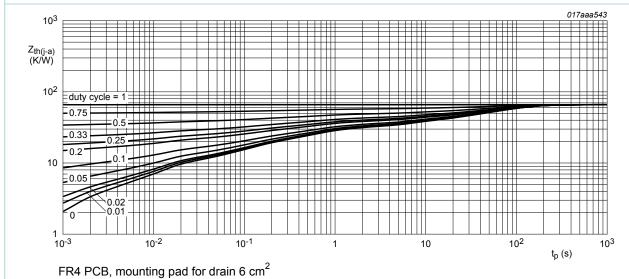
| Symbol                | Parameter  | Conditions |     | Min | Тур | Max | Unit |
|-----------------------|--|------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub>  | thermal resistance                               |            | [1] | -   | 235 | 270 | K/W  |
|                       | from junction to ambient                         |            | [2] | -   | 67  | 74  | K/W  |
| R <sub>th(j-sp)</sub> | thermal resistance from junction to solder point |            |     | -   | 5   | 10  | K/W  |

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 5.

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## 10. Characteristics

#### Table 7. Characteristics

| Symbol               | Parameter                         | Conditions  | Min | Тур  | Max  | Unit |
|----------------------|-----------------------------------|---|-----|------|------|------|
| Static chara         | acteristics                       |   |     |      |      | ,    |
| V <sub>(BR)DSS</sub> | drain-source<br>breakdown voltage | $I_D$ = -250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C                       | -30 | -    | -    | V    |
| $V_{GSth}$           | gate-source threshold voltage     | $I_D$ = -250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C                 | -1  | -1.5 | -2.5 | V    |
| I <sub>DSS</sub>     | drain leakage current             | $V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$       | -   | -    | -1   | μA   |
| I <sub>GSS</sub>     | gate leakage current              | $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | -   | -    | -100 | nA   |
|                      |                                   | V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C     | -   | -    | 100  | nA   |
| R <sub>DSon</sub>    | drain-source on-state             | $V_{GS}$ = -10 V; $I_D$ = -4.7 A; $T_j$ = 25 °C                           | -   | 40   | 50   | mΩ   |
| re                   | resistance                        | V <sub>GS</sub> = -10 V; I <sub>D</sub> = -4.7 A; T <sub>j</sub> = 150 °C | -   | 60   | 75   | mΩ   |
|                      |                                   | $V_{GS}$ = -4.5 V; $I_D$ = -3.9 A; $T_j$ = 25 °C                          | -   | 55   | 76   | mΩ   |
| 9 <sub>fs</sub>      | forward transconductance          | $V_{DS}$ = -10 V; $I_D$ = -4.7 A; $T_j$ = 25 °C                           | -   | 15   | -    | S    |
| R <sub>G</sub>       | gate resistance                   | f = 1 MHz   | -   | 6    | -    | Ω    |
| Dynamic ch           | naracteristics                    |   |     |      | -    |      |
| Q <sub>G(tot)</sub>  | total gate charge                 | $V_{DS}$ = -15 V; $I_{D}$ = -4.7 A; $V_{GS}$ = -10 V;                     | -   | 17   | 26   | nC   |
| Q <sub>GS</sub>      | gate-source charge                | T <sub>j</sub> = 25 °C  | -   | 2.5  | -    | nC   |
| $Q_{GD}$             | gate-drain charge                 |   | -   | 3.2  | -    | nC   |
| C <sub>iss</sub>     | input capacitance                 | V <sub>DS</sub> = -15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;                | -   | 860  | -    | pF   |
| C <sub>oss</sub>     | output capacitance                | T <sub>j</sub> = 25 °C  | -   | 105  | -    | pF   |
| C <sub>rss</sub>     | reverse transfer capacitance      |   | -   | 87   | -    | pF   |
| t <sub>d(on)</sub>   | turn-on delay time                | $V_{DS}$ = -15 V; $I_{D}$ = -4.7 A; $V_{GS}$ = -10 V;                     | -   | 7.4  | -    | ns   |
| t <sub>r</sub>       | rise time                         | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$                                      | -   | 17.5 | -    | ns   |
| t <sub>d(off)</sub>  | turn-off delay time               |   | -   | 27   | -    | ns   |
| t <sub>f</sub>       | fall time                         |   | -   | 10.4 | -    | ns   |
| Source-dra           | in diode                          |   | ,   |      |      |      |
| $V_{SD}$             | source-drain voltage              | $I_S = -1.8 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$   | -   | -0.8 | -1.2 | V    |
| t <sub>rr</sub>      | reverse recovery time             | $I_S = -1.8 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s};$              | -   | 11   | -    | ns   |
| Q <sub>r</sub>       | recovered charge                  | $V_{GS} = 0 \text{ V}; V_{DS} = -15 \text{ V}; T_j = 25 \text{ °C}$       | -   | 4    | -    | nC   |

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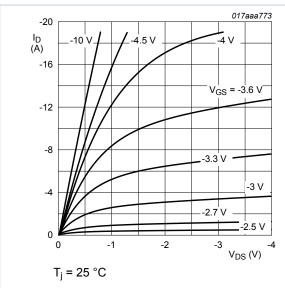


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

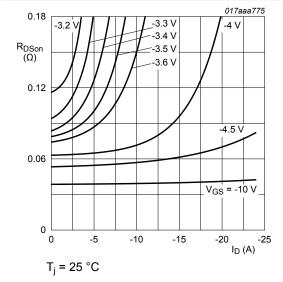


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

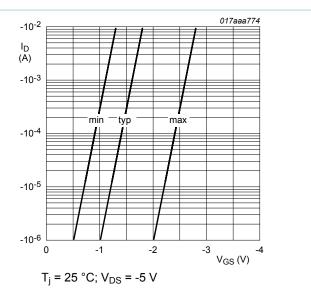


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

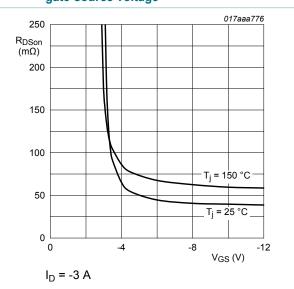


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 30 V, P-channel Trench MOSFET

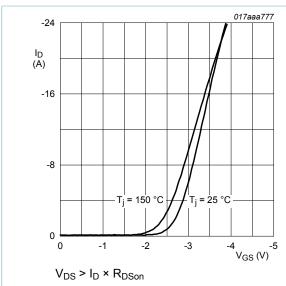


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

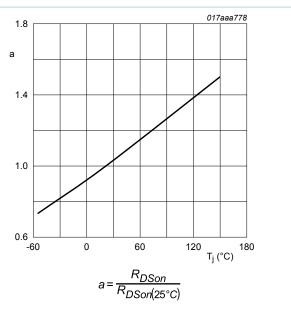


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

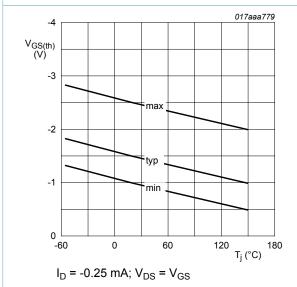


Fig. 12. Gate-source threshold voltage as a function of junction temperature

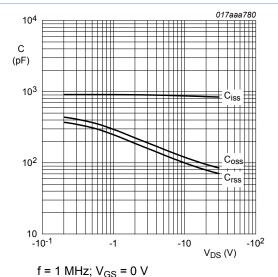


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

#### 30 V, P-channel Trench MOSFET

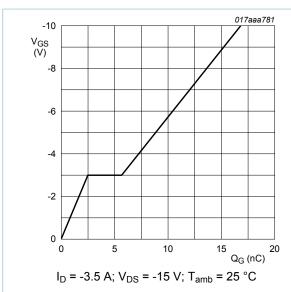


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$ 

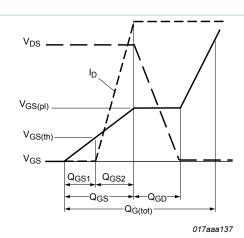


Fig. 15. Gate charge waveform definitions

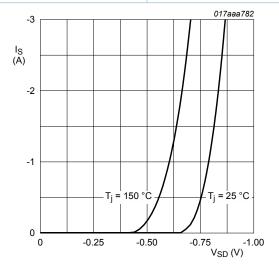
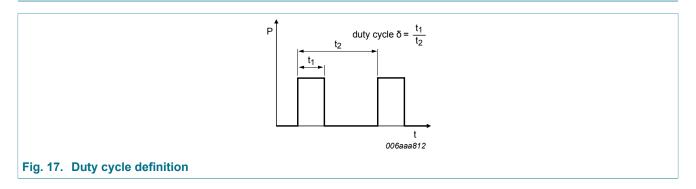


Fig. 16. Source current as a function of source-drain voltage; typical values

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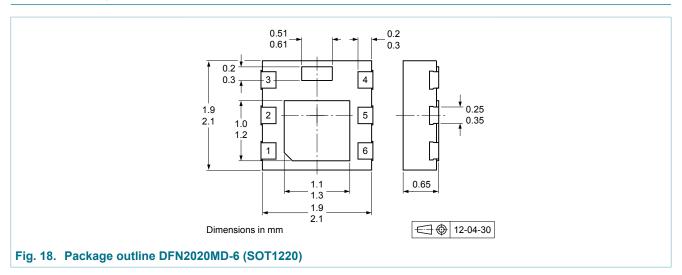
### 11. Test information



### **Quality information**

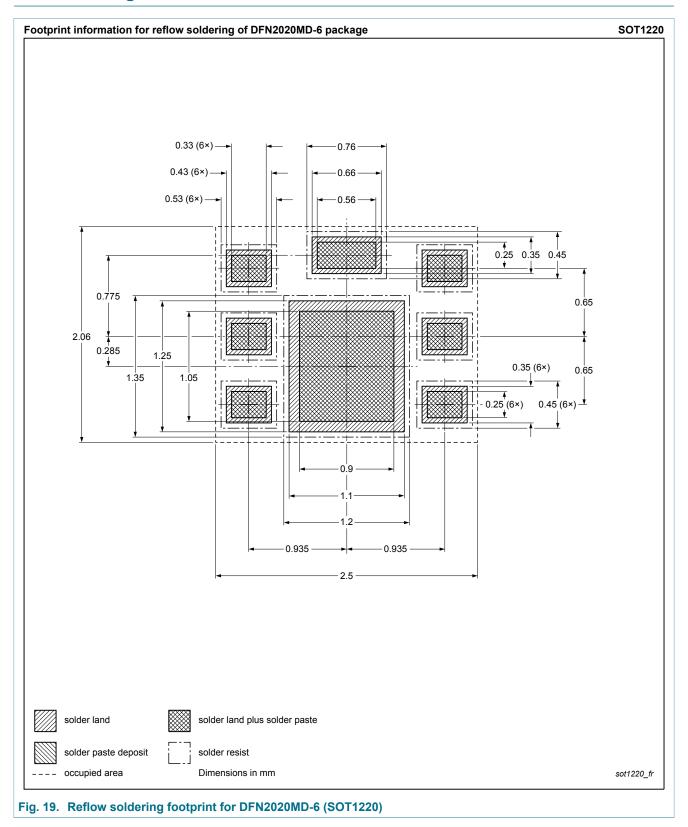
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 12. Package outline



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# 13. Soldering



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# 14. Revision history

#### **Table 8. Revision history**

| Data sheet ID | Release date | Data sheet status  | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| PMPB48EPA v.1 | 20180327     | Product data sheet | -             | -          |

#### 30 V, P-channel Trench MOSFET

# 15. Legal information

#### **Data sheet status**

| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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